

# Gabriel Ferro

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1545148/publications.pdf>

Version: 2024-02-01

174  
papers

1,676  
citations

331259

21  
h-index

377514

34  
g-index

174  
all docs

174  
docs citations

174  
times ranked

1613  
citing authors

#	ARTICLE	IF	CITATIONS
1	Evidence for Flat Bands near the Fermi Level in Epitaxial Rhombohedral Multilayer Graphene. ACS Nano, 2015, 9, 5432-5439.	7.3	92
2	A Vaporâ€“Liquidâ€“Solid Mechanism for Growing 3C-SiC Single-Domain Layers on 6H-SiC(0001). Advanced Functional Materials, 2006, 16, 975-979.	7.8	86
3	3C-SiC Heteroepitaxial Growth on Silicon: The Quest for Holy Grail. Critical Reviews in Solid State and Materials Sciences, 2015, 40, 56-76.	6.8	69
4	Photonic crystal cavities in cubic (3C) polytype silicon carbide films. Optics Express, 2013, 21, 32623.	1.7	65
5	Growth by a vapourâ€“liquidâ€“solid mechanism: a new approach for silicon carbide epitaxy. New Journal of Chemistry, 2004, 28, 889-896.	1.4	54
6	Critically coupled surface phonon-polariton excitation in silicon carbide. Optics Letters, 2009, 34, 2667.	1.7	53
7	Nanodiamond Integration with Photonic Devices. Laser and Photonics Reviews, 2019, 13, 1800316.	4.4	50
8	A comprehensive study of SiC growth processes in a VPE reactor. Thin Solid Films, 2002, 402, 83-89.	0.8	46
9	Hybrid Group IV Nanophotonic Structures Incorporating Diamond Silicon-Vacancy Color Centers. Nano Letters, 2016, 16, 212-217.	4.5	46
10	Midinfrared Index Sensing of pL-Scale Analytes Based on Surface Phonon Polaritons in Silicon Carbide. Journal of Physical Chemistry C, 2010, 114, 7489-7491.	1.5	45
11	Direct synthesis of $\hat{\Gamma}^2$ -SiC and h-BN coated $\hat{\Gamma}^2$ -SiC nanowires. Solid State Communications, 2002, 124, 157-161.	0.9	42
12	Visible Photoluminescence from Cubic (3C) Silicon Carbide Microdisks Coupled to High Quality Whispering Gallery Modes. ACS Photonics, 2015, 2, 14-19.	3.2	42
13	Vaporâ€“Liquidâ€“Solid Growth of 3C-SiC on $\hat{\Gamma}^2$ -SiC Substrates. 1. Growth Mechanism. Crystal Growth and Design, 2008, 8, 1044-1050.	1.4	40
14	Measurements of the negative refractive index of sub-diffraction waves propagating in an indefinite permittivity medium. Optics Express, 2010, 18, 22734.	1.7	40
15	Strain Tailoring in 3C-SiC Heteroepitaxial Layers Grown on Si(100). Chemical Vapor Deposition, 2006, 12, 483-488.	1.4	37
16	Characterization of a 3C-SiC Single Domain Grown on 6H-SiC(0001) by a Vaporâ€“Liquidâ€“Solid Mechanism. Crystal Growth and Design, 2006, 6, 2598-2602.	1.4	30
17	On the growth of 4Hâ€“SiC by low-temperature liquid phase epitaxy in Al rich Alâ€“Si melts. Journal of Crystal Growth, 2003, 254, 123-130.	0.7	26
18	Highly Confined Hybrid Spool Surface Plasmons in Ultrathin Metal-Dielectric Heterostructures. Physical Review Letters, 2010, 105, 176803.	2.9	26

#	ARTICLE	IF	CITATIONS
19	Nucleation of 3C-SiC on 6H-SiC from a liquid phase. <i>Acta Materialia</i> , 2007, 55, 6873-6880.	3.8	25
20	A Study on the Temperature of Ohmic Contact to p-Type SiC Based on $Ti_{3-x}Si_x$ Phase. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2462-2468.	1.6	25
21	From Si nanowire to SiC nanotube. <i>Journal of Nanoparticle Research</i> , 2011, 13, 5425-5433.	0.8	23
22	How to Grow Unstrained 3C-SiC Heteroepitaxial Layers on Si (100) Substrates. <i>Materials Science Forum</i> , 2001, 353-356, 155-158.	0.3	22
23	Very Low Interface State Density From Thermally Oxidized Single-Domain 3C-SiC/6H-SiC Grown by Vapor-Liquid-Solid Mechanism. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 6823-6829.	0.8	21
24	The (001) 3C SiC surface termination and band structure after common wet chemical etching procedures, studied by XPS, LEED, and HREELS. <i>Applied Surface Science</i> , 2018, 427, 480-485.	3.1	21
25	Improved Ni/3C-SiC contacts by effective contact area and conductivity increases at the nanoscale. <i>Applied Physics Letters</i> , 2009, 94, 112104.	1.5	20
26	Study of the 3C-SiC nucleation from a liquid phase on a C face 6H-SiC substrate. <i>Journal of Crystal Growth</i> , 2009, 311, 2385-2390.	0.7	19
27	A new model for in situ nitrogen incorporation into 4H-SiC during epitaxy. <i>Scientific Reports</i> , 2017, 7, 43069.	1.6	19
28	Two-dimensional defect mapping of the $SiO_2/SiC$ interface. <i>Physical Review Materials</i> , 2019, 3, .	0.9	19
29	Flash Lamp Supported Deposition of 3C-SiC (FLASiC) – a Promising Technique to Produce High Quality Cubic SiC Layers. <i>Materials Science Forum</i> , 2004, 457-460, 175-180.	0.3	18
30	RHEED monitoring of AlN epitaxial growth by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2000, 210, 429-434.	0.7	16
31	Vapor-Liquid-Solid Growth of 3C-SiC on $\pm$ -SiC Substrates. 2. Growth Kinetics. <i>Crystal Growth and Design</i> , 2008, 8, 1051-1054.	1.4	16
32	Sublimation Growth and Structural Characterization of 3C-SiC on Hexagonal and Cubic SiC Seeds. <i>Materials Science Forum</i> , 0, 645-648, 175-178.	0.3	16
33	Deposition of nanocrystalline translucent h-BN films by chemical vapor deposition at high temperature. <i>Thin Solid Films</i> , 2012, 520, 2424-2428.	0.8	16
34	Ge incorporation inside 4H-SiC during homoepitaxial growth by chemical vapor deposition. <i>Acta Materialia</i> , 2014, 75, 219-226.	3.8	16
35	Growth mode of AlN epitaxial layers on 6H-SiC by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2000, 209, 415-418.	0.7	13
36	Buried Selective Growth of p-Doped SiC by VLS Epitaxy. <i>Materials Science Forum</i> , 0, 717-720, 169-172.	0.3	13

#	ARTICLE	IF	CITATIONS
37	Aluminium-Silicon as a Melt for the Low Temperature Growth of SiC Crystals. Materials Science Forum, 2001, 353-356, 85-90.	0.3	12
38	Overview of 3C-SiC Crystalline Growth. Materials Science Forum, 0, 645-648, 49-54.	0.3	12
39	SiC Homoepitaxial Growth at Low Temperature by Vapor-Liquid-Solid Mechanism in Al-Si Melt. Crystal Growth and Design, 2003, 3, 285-287.	1.4	11
40	Nanoscale probing of dielectric breakdown at SiO <sub>2</sub> /3C-SiC interfaces. Journal of Applied Physics, 2011, 109, .	1.1	11
41	Prism-coupled surface wave accelerator based on silicon carbide. Physical Review Special Topics: Accelerators and Beams, 2012, 15, .	1.8	11
42	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. Materials Science Forum, 0, 778-780, 706-709.	0.3	11
43	Effect of the Si Droplet Size on the VLS Growth Mechanism of SiC Homoepitaxial Layers. Materials Science Forum, 2002, 389-393, 287-290.	0.3	10
44	Improved SiCOI Structures Elaborated by Heteroepitaxy of 3C-SiC on SOI. Materials Science Forum, 2002, 389-393, 343-346.	0.3	10
45	AlN hollow-nanofilaments by electrospinning. Nanotechnology, 2015, 26, 085603.	1.3	10
46	Growth Mode and Kinetics of Atmospheric Pressure Chemical Vapour Deposition of $\beta$ -SiC on Si(100) Substrate. Materials Science Forum, 1998, 264-268, 227-230.	0.3	9
47	Searching for Ge Clusters inside 3C-SiC Layers Grown by Vapor-Liquid-Solid Mechanism on 6H-SiC Substrates. Materials Science Forum, 2009, 615-617, 185-188.	0.3	9
48	Incorporation of group III, IV and V elements in 3C-SiC(111) layers grown by the vapour-liquid-solid mechanism. Journal of Crystal Growth, 2010, 312, 3443-3450.	0.7	9
49	Growth of silicon oxide nanowires at low temperature using tin hydroxide catalyst. Journal of Crystal Growth, 2011, 320, 55-62.	0.7	9
50	Growth and Characterisation of Heavily Al-Doped 4H-SiC Layers Grown by VLS in an Al-Si Melt. Materials Science Forum, 2004, 457-460, 735-738.	0.3	8
51	Optical Investigation of Cubic SiC Layers Grown on Hexagonal SiC Substrates by CVD and VLS. Materials Science Forum, 2007, 556-557, 403-406.	0.3	8
52	Low Doped 3C-SiC Layers Deposited by the Vapour-Liquid-Solid Mechanism on 6H-SiC Substrates. Materials Science Forum, 0, 645-648, 171-174.	0.3	8
53	Electrical Characterization of p <sup>+</sup> Layer Selectively Grown by VLS Transport. Materials Science Forum, 2013, 740-742, 911-914.	0.3	8
54	Development and Characterization of Inorganic Scintillating Fibers Made of LuAG:Ce and LYSO:Ce. IEEE Transactions on Nuclear Science, 2014, 61, 353-361.	1.2	8

#	ARTICLE	IF	CITATIONS
55	Nature effect of the gas during high temperature treatments of 4H-SiC substrates. Applied Surface Science, 2003, 207, 200-207.	3.1	7
56	Probing the effect of temperature on the incorporation of Al species in a SiC matrix. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1265-1268.	0.8	7
57	Investigation of 3C-SiC(111) Homoepitaxial Growth by CVD at High Temperature. Materials Science Forum, 0, 645-648, 127-130.	0.3	7
58	On the Mechanism of Twin Boundary Elimination in 3C-SiC(111) Heteroepitaxial Layers on $\hat{1}\pm$ -SiC Substrates. Materials Science Forum, 0, 679-680, 71-74.	0.3	7
59	Characterization of Ge-Doped Homoepitaxial Layers Grown by Chemical Vapor Deposition. Materials Science Forum, 2014, 778-780, 261-264.	0.3	7
60	4H-SiC(0001) Surface Faceting during Interaction with Liquid Si. Materials Science Forum, 0, 858, 163-166.	0.3	7
61	Analysis of 4H-SiC MOS Capacitors on Macro-Stepped Surfaces. Materials Science Forum, 0, 897, 107-110.	0.3	7
62	Comparative Evaluation of Free-Standing 3C-SiC Crystals. Materials Science Forum, 2005, 483-485, 229-232.	0.3	6
63	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. Materials Science Forum, 2006, 527-529, 287-290.	0.3	6
64	Growth of SiC from a Liquid Phase at Low Temperature. Materials Science Forum, 2007, 556-557, 41-46.	0.3	6
65	Optical Study of Ge Incorporation in Cubic SiC Layers Grown by VLS. Materials Science Forum, 2008, 600-603, 529-532.	0.3	6
66	Optical Characterization of VLS+CVD Grown 3C-SiC Films by Non-Linear and Photoluminescence Techniques. Materials Science Forum, 2010, 645-648, 443-446.	0.3	6
67	Detailed study of the influence of surface misorientation on the density of Anti-Phase Boundaries in 3C-SiC layers grown on (001) silicon. , 2010, , .		6
68	MOS Capacitors Fabricated on 3C-SiC(111) Layers Grown on 6H-SiC(0001). Journal of the Electrochemical Society, 2011, 158, H630.	1.3	6
69	Checker-Board Carbonization for Control and Reduction of the Mean Curvature of 3C-SiC Layers Grown on Si(100) Substrates. Materials Science Forum, 2004, 457-460, 265-268.	0.3	5
70	Investigation of Thick 3C-SiC Films Re-Grown on Thin 35 nm "Flash Lamp Annealed" 3C-SiC Layers. Materials Science Forum, 2004, 457-460, 313-316.	0.3	5
71	Microstructural Characterization of 3C-SiC Thin Films Grown by Flash Lamp Induced Liquid Phase Epitaxy. Materials Science Forum, 2005, 483-485, 295-298.	0.3	5
72	Evolution of 3C-SiC islands nucleated from a liquid phase on Si face $\hat{1}\pm$ -SiC substrates. Thin Solid Films, 2010, 518, 4234-4241.	0.8	5

#	ARTICLE	IF	CITATIONS
73	Is the Liquid Phase a Viable Approach for Bulk Growth of 3C-SiC?. Materials Science Forum, 2010, 645-648, 67-70.	0.3	5
74	3C-SiC MOS Based Devices: From Material Growth to Device Characterization. Materials Science Forum, 0, 679-680, 433-436.	0.3	5
75	Ge Assisted SiC Epitaxial Growth by CVD on SiC Substrate. Materials Science Forum, 0, 778-780, 187-192.	0.3	5
76	Growth and Characterization of Undoped Polysilicon Thick Layers: Revisiting an Old System. Silicon, 2020, 12, 1187-1194.	1.8	5
77	Structural Characterization of Thin 3C-SiC Films Annealed by the Flash Lamp Process. Materials Science Forum, 2004, 457-460, 351-354.	0.3	4
78	Is the Al Solubility Limit in SiC Temperature Dependent or not?. Materials Science Forum, 2005, 483-485, 125-128.	0.3	4
79	Electrical Characterisation of Heavily Al Doped 4H-SiC Layer Grown by Vapour-Liquid-Solid Epitaxy in Al-Si Melt. Materials Science Forum, 2005, 483-485, 421-424.	0.3	4
80	Effect of the Crystallization Conditions on the Epitaxial Relationship of Si Deposited on 3C-SiC(100). Materials Science Forum, 2006, 527-529, 1563-1566.	0.3	4
81	Boron Doping during Vapor-Liquid-Solid Growth of Homoepitaxial 4H-SiC Layers. Materials Science Forum, 2007, 556-557, 65-68.	0.3	4
82	Defect-induced polytype transformations in LPE grown SiC epilayers on (111) 3C-SiC seeds grown by VLS on 6H-SiC. Physica B: Condensed Matter, 2009, 404, 4727-4730.	1.3	4
83	Further Evidence of Nitrogen Induced Stabilization of 3C-SiC Polytype during Growth from a Si-Ge Liquid Phase. Materials Science Forum, 0, 645-648, 163-166.	0.3	4
84	Influence of the C/Si Ratio on the Dopant Concentration and Defects in CVD Grown 3C-SiC Homoepitaxial Layers. AIP Conference Proceedings, 2010, , .	0.3	4
85	Effect of nitrogen impurity on the stabilization of 3C-SiC polytype during heteroepitaxial growth by vapor-liquid-solid mechanism on 6H-SiC substrates. Diamond and Related Materials, 2011, 20, 808-813.	1.8	4
86	Investigation of 3C-SiC growth on Si(111) by vapor-liquid-solid transport using a SiGe liquid phase. Journal of Crystal Growth, 2012, 354, 119-128.	0.7	4
87	Growth of aluminum nitride on flat and patterned Si (111) by high temperature halide CVD. Thin Solid Films, 2017, 623, 65-71.	0.8	4
88	Interfacial Strain and Defects in Si (001) Carbonization Layers for 3C-SiC Hetero-Epitaxy. Materials Science Forum, 2004, 457-460, 277-280.	0.3	3
89	How to Grow 3C-SiC Single Domain on Si-SiC(0001) by Vapor-Liquid-Solid Mechanism. Materials Science Forum, 2007, 556-557, 187-190.	0.3	3
90	Properties of 3C-SiC Grown by Sublimation Epitaxy on Different Type of Substrates. Materials Science Forum, 2010, 645-648, 183-186.	0.3	3

#	ARTICLE	IF	CITATIONS
91	LTPL Investigation of N-Ga and N-Al Donor-Acceptor Pair Spectra in 3C-SiC Layers Grown by VLS on 6H-SiC Substrates. Materials Science Forum, 0, 645-648, 415-418.	0.3	3
92	Growth of Nanocrystalline Translucent h-BN Films Deposited by CVD at High Temperature on SiC Substrates. Materials Science Forum, 0, 645-648, 1191-1194.	0.3	3
93	Defects in (111) 3C-SiC layers grown at different temperatures by VLS and CVD on 6H-SiC substrates. , 2010, , .		3
94	Growing 3C-SiC heteroepitaxial layers on $\hat{1}\hat{1}$ -SiC substrate by vapour-liquid-solid mechanism from the Al-Ge-Si ternary system. Journal of Crystal Growth, 2011, 318, 397-400.	0.7	3
95	Surface Morphology Evolution after Epitaxial Growth on $4^{\circ}$ Off-Axis 4H-SiC Substrate. Materials Science Forum, 2012, 717-720, 145-148.	0.3	3
96	Influence of Ga doping on the microstructure of 3C-SiC layers grown on 4H-SiC substrates by VLS mechanism. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 72-75.	0.8	3
97	p-Doped SiC Growth on Diamond Substrate by VLS Transport. Materials Science Forum, 0, 740-742, 331-334.	0.3	3
98	Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts. Materials Science Forum, 0, 778-780, 639-644.	0.3	3
99	A Study on the Chemistry of Epitaxial Ti <sub>3</sub> SiC <sub>2</sub> Formation on 4H-SiC Using Al-Ti Annealing. Materials Science Forum, 0, 821-823, 432-435.	0.3	3
100	Silicon Deposition on 3C-SiC Seeds of Different Orientations. Materials Science Forum, 0, 897, 87-90.	0.3	3
101	Highly Mg-doped GaN dots and films grown by VLS transport at low temperature. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600428.	0.8	3
102	Understanding Al incorporation into 4H-SiC during epitaxy. Journal of Crystal Growth, 2019, 507, 338-343.	0.7	3
103	Macrosteps formation on 4H-SiC surfaces via Si melting within a sandwich configuration. Journal of Crystal Growth, 2022, 593, 126783.	0.7	3
104	SiO <sub>2</sub> as Oxygen Source for the Chemical Vapor Transport of SiC. Materials Science Forum, 2002, 389-393, 307-310.	0.3	2
105	Formation of 3C-SiC Films Embedded in SiO <sub>2</sub> by Sacrificial Oxidation. Materials Science Forum, 2004, 457-460, 1515-1518.	0.3	2
106	Analysis of SiC Islands Formation during First Steps of Si Carbonization Process. Materials Science Forum, 2005, 483-485, 555-558.	0.3	2
107	TEM and LTPL Investigations of 3C-SiC Layers Grown by LPE on (100) and (111) 3C-SiC Seeds. Materials Science Forum, 0, 645-648, 383-386.	0.3	2
108	Elaboration and characterization of boron doping during SiC growth by VLS mechanism. Journal of Crystal Growth, 2011, 327, 46-51.	0.7	2

#	ARTICLE	IF	CITATIONS
109	Investigation of 3C-SiC Lateral Growth on 4H-SiC Mesas. Materials Science Forum, 0, 679-680, 111-114.	0.3	2
110	Influence of Post-Growth Annealing on the Defects Nature and Distribution in VLS Grown (111) 3C-SiC Layers. Materials Science Forum, 2011, 679-680, 241-244.	0.3	2
111	Seeding Layer Influence on the Low Temperature Photoluminescence Intensity of 3C-SiC Grown on 6H-SiC by Sublimation Epitaxy. Materials Science Forum, 2012, 711, 149-153.	0.3	2
112	On the Formation of Graphene by Ge Intercalation of a 4H-SiC Surface. Materials Science Forum, 2015, 821-823, 961-964.	0.3	2
113	Characterization and Applications of New High Quality LuAG:Ce and LYSO:Ce fibers. Journal of Physics: Conference Series, 2015, 587, 012067.	0.3	2
114	Behavior and Chemical Reactions of Liquid Si and Ge on SiD <sub>j</sub> Surface. Materials Science Forum, 0, 821-823, 121-124.	0.3	2
115	Optimization of VLS Growth Process for 4H-SiC P/N Junctions. Materials Science Forum, 0, 858, 205-208.	0.3	2
116	Growth and doping of silicon carbide with germanium: a review. Critical Reviews in Solid State and Materials Sciences, 2022, 47, 520-537.	6.8	2
117	Liquid Si-Induced 4H-SiC Surface Structuring Using a Sandwich Configuration. Materials Science Forum, 0, 1062, 8-12.	0.3	2
118	Control of the 2D/3D Transition of Cubic GaN/AlN Nanostructures on 3C-SiC Epilayers. Materials Science Forum, 2004, 457-460, 1561-1564.	0.3	1
119	Comparison of Different Metal Additives to Si for the Homoepitaxial Growth of 4H-SiC Layers by Vapour-Liquid-Solid Mechanism. Materials Science Forum, 2004, 457-460, 245-248.	0.3	1
120	Using Vapour-Liquid-Solid Mechanism for SiC Homoepitaxial Growth on on-axis 4H-SiC (0001) at Low Temperature. Materials Science Forum, 2006, 527-529, 271-274.	0.3	1
121	Reliability of Thin Thermally Grown SiO <sub>2</sub> on 3C-SiC Studied by Scanning Probe Microscopy. Materials Science Forum, 0, 645-648, 833-836.	0.3	1
122	Electrical properties of MOS structures based on 3C-SiC(111) epilayers grown by Vapor-Liquid-Solid Transport and Chemical-Vapor Deposition on 6H-SiC(0001). AIP Conference Proceedings, 2010, , .	0.3	1
123	Deep levels in hetero-epitaxial as-grown 3C-SiC. , 2010, , .		1
124	Investigation of the Growth of 3C-SiC on Si by Vapor-Liquid-Solid ( VLS ) Transport. Materials Science Forum, 2011, 679-680, 99-102.	0.3	1
125	New Approaches to In Situ Doping of SiC Epitaxial Layers. Advanced Materials Research, 0, 324, 14-19.	0.3	1
126	Nondestructive Evaluation of Photo-Electrical Properties of 3C-SiC (111) Homoepitaxial Layers Grown by CVD. Materials Science Forum, 0, 679-680, 153-156.	0.3	1



#	ARTICLE	IF	CITATIONS
127	Structural and Optical Investigation of VLS Grown (111) 3C-SiC Layers on 6H-SiC Substrates in Sn-Based Melts. Materials Science Forum, 0, 679-680, 165-168.	0.3	1
128	On Applicability of Time-Resolved Optical Techniques for Characterization of Differently Grown 3C-SiC Crystals and Heterostructures. Materials Science Forum, 2012, 711, 159-163.	0.3	1
129	Study of the Nucleation of p-Doped SiC in Selective Epitaxial Growth Using VLS Transport. Materials Science Forum, 2013, 740-742, 177-180.	0.3	1
130	Heteroepitaxial CVD Growth of 3C-SiC on Diamond Substrate. Materials Science Forum, 2014, 778-780, 226-229.	0.3	1
131	Characterization and optimization of new high-quality inorganic fibers made of LuAG:Ce and LYSO:Ce. , 2014, , .		1
132	VLS Grown 4H-SiC Buried P <sup>+</sup> Layers for JFET Lateral Structures. Materials Science Forum, 2015, 821-823, 789-792.	0.3	1
133	Visible Photoluminescence in Cubic (3C) Silicon Carbide Coupled to High Quality Microdisk Resonators. , 2015, , .		1
134	Understanding of the Growth Mechanism Leading to Twin Boundary Elimination during 3C-SiC Heteroepitaxy on 4H-SiC Substrate by CVD. Materials Science Forum, 2015, 821-823, 209-212.	0.3	1
135	MOS Interface Characteristics of <i>In Situ</i> Ge-Doped 4H-SiC Homoepitaxial Layers. Materials Science Forum, 2015, 821-823, 512-515.	0.3	1
136	Optimization of the Silicidation and Growth Processes for 3C-SiC Heteroepitaxy on Diamond Substrate. Materials Science Forum, 2016, 858, 155-158.	0.3	1
137	Thermally Stable Ohmic Contact to p-Type 4H-SiC Based on Ti <sub>3</sub> SiC <sub>2</sub> Phase. Materials Science Forum, 0, 858, 553-556.	0.3	1
138	Low temperature homoepitaxy of GaN structures by Vapor Liquid Solid transport. Journal of Crystal Growth, 2017, 467, 18-28.	0.7	1
139	Very High Sustainable Forward Current Densities on 4H-SiC p-n Junctions Formed by VLS Localized Epitaxy of Heavily Al-Doped p <sup>+</sup> Emitters. Materials Science Forum, 2017, 897, 63-66.	0.3	1
140	Diamond Color Center Integration with a Silicon Carbide Photonics Platform. , 2018, , .		1
141	Thermochromic properties of some colored oxide materials. Optical Materials: X, 2022, 15, 100167.	0.3	1
142	Potential of HMDS/C <sub>3</sub> H <sub>8</sub> Precursor System for the Growth of State of the Art Heteroepitaxial 3C-SiC Layers on Si(100). Materials Science Forum, 2004, 457-460, 281-284.	0.3	0
143	Planar Defects, Voids and their Relationship in 3C-SiC Layers. Materials Science Forum, 2005, 483-485, 189-192.	0.3	0
144	Nano-Electro-Structural Evolution of Ni-Si Ohmic Contacts to 3C-SiC. Materials Science Forum, 2009, 615-617, 569-572.	0.3	0

#	ARTICLE	IF	CITATIONS
145	Effects of Temperature and Heating Rate on the Precipitation of 3C-SiC Islands on 4H-SiC(0001) from a Liquid Phase. Materials Science Forum, 2009, 615-617, 193-196.	0.3	0
146	Critically coupled surface phonon-polariton excitation in silicon carbide. , 2009, , .		0
147	Effects of Growth Conditions on the Low Temperature Photoluminescence Spectra of (111) 3C-SiC Layers Grown by Chemical Vapor Deposition on 3C-SiC Seeds grown by the Vapor-Liquid-Solid Technique. , 2010, , .		0
148	Growing p-type 3C-SiC heteroepitaxial layers by Vapour-Liquid-Solid mechanism on 6H-SiC substrate. , 2010, , .		0
149	Structural Evolution of 3C-SiC Grown by Sublimation Epitaxy. , 2010, , .		0
150	TEM investigation of the influence of the Ga-doping on the structure of 3C-SiC layers grown on 6H-SiC substrate by VLS mechanism. , 2010, , .		0
151	Splitting of close N-Al donor-acceptor-pair spectra in 3C-SiC. , 2010, , .		0
152	Rapid Thermal Oxynitridation and Hydrogenation of 3C-SiC $\hat{\cdot}$ Si using N[sub 2]O and H[sub 2] Ambient. , 2010, , .		0
153	On the Characterization of Boron in BGeAs Nano-Films Using IBA Techniques. Advanced Materials Research, 2011, 324, 314-317.	0.3	0
154	On the Quantification of Al Incorporated in SiC Material Using Particle Induced X-Ray Emission Technique. Materials Science Forum, 0, 679-680, 189-192.	0.3	0
155	On the Characterization of Ultra Thin Al Films Deposited onto SiC Substrate Using PIXE Technique. Advanced Materials Research, 2011, 324, 302-305.	0.3	0
156	Epitaxial Growth of 3C-SiC onto Silicon Substrate by VLS Transport Using CVD-Grown 3C-SiC Seeding Layer. Materials Science Forum, 0, 711, 35-39.	0.3	0
157	Elimination of Twin Boundaries when Growing 3C-SiC Heteroepitaxial by Vapour-Liquid-Solid Mechanism on Patterned 4H-SiC Substrate. Materials Science Forum, 0, 711, 11-15.	0.3	0
158	Study of the Lateral Growth by VLS Mechanism Using Al-Based Melts on Patterned SiD <sub>j</sub> Substrate. Materials Science Forum, 2012, 717-720, 165-168.	0.3	0
159	Elaboration of Core Si/Shell SiC Nanowires. Materials Science Forum, 0, 740-742, 306-310.	0.3	0
160	Exploring SiC Growth Limitation of Vapor-Liquid-Solid Mechanism when Using Two Different Carbon Precursors. Materials Science Forum, 2013, 740-742, 323-326.	0.3	0
161	Characterisation of new inorganic fibers made of LuAG:Ce and LYSO:Ce. , 2013, , .		0
162	Ge Assisted 3C-SiC Nucleation and Growth by Vapour Phase Epitaxy on On-Axis 4H-SiC Substrate. Materials Science Forum, 2014, 806, 27-31.	0.3	0

#	ARTICLE	IF	CITATIONS
163	3C-SiC Seeded Growth on Diamond Substrate by VLS Transport. Materials Science Forum, 2014, 778-780, 234-237.	0.3	0
164	Heteroepitaxy of P-Doped 3C-SiC on Diamond by VLS Transport. Materials Science Forum, 0, 806, 33-37.	0.3	0
165	Improvement of the Specific Contact Resistance on P-Type 4H-SiC by Using a Highly P-Typed Doped 4H-SiC Layer Selectively Grown by VLS Transport. Materials Science Forum, 2014, 806, 57-60.	0.3	0
166	Hybrid Diamond-Silicon Carbide Structures Incorporating Silicon-Vacancies in Diamond as Quantum Emitters. , 2015, , .		0
167	Ge Addition during 4H-SiC Epitaxial Growth by CVD: Mechanism of Incorporation. Materials Science Forum, 2015, 821-823, 115-120.	0.3	0
168	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. Materials Science Forum, 2015, 821-823, 424-427.	0.3	0
169	3C-SiC Microdisks for Visible Photonics. Materials Science Forum, 0, 858, 711-714.	0.3	0
170	Silicon (001) Heteroepitaxy on 3C-SiC(001)/Si(001) Seed. Materials Science Forum, 2018, 924, 128-131.	0.3	0
171	How to Grow Fully (100) Oriented SiC/Si/SiC/Si Multi-Stack. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800588.	0.8	0
172	Spatially-Resolved Evaluation of Interface Defect Density on Macrostepped SiO <sub>2</sub> /SiC using Local Deep Level Transient Spectroscopy. , 2019, , .		0
173	Nanophotonics in novel 2D-materials: (111)-GaAs and 3C-SiC. , 2015, , .		0
174	Emitter-Cavity Coupling in Hybrid Silicon Carbide-Nanodiamond Microdisk Resonators. , 2016, , .		0